



N-Channel 200-V (D-S) 150°C MOSFET

CHARACTERISTICS

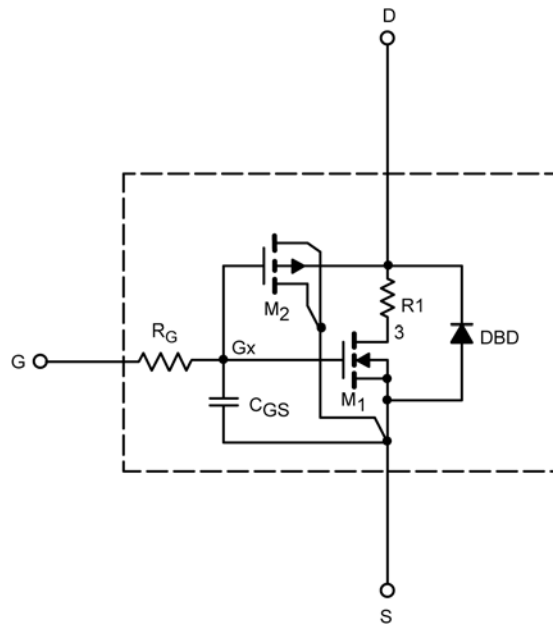
- N-Channel Vertical DMOS
- Macro Model (Subcircuit Model)
- Level 3 MOS
- Apply for both Linear and Switching Application
- Accurate over the -55 to 125°C Temperature Range
- Model the Gate Charge, Transient, and Diode Reverse Recovery Characteristics

DESCRIPTION

The attached spice model describes the typical electrical characteristics of the n-channel vertical DMOS. The subcircuit model is extracted and optimized over the -55 to 125°C temperature ranges under the pulsed 0-V to 15-V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage.

A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched C_{gd} model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

SUBCIRCUIT MODEL SCHEMATIC



This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.

SPICE Device Model SUP33N20-60P



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SPECIFICATIONS (T _J = 25°C UNLESS OTHERWISE NOTED)					
Parameter	Symbol	Test Condition	Simulated Data	Measured Data	Unit
Static					
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	2.4		V
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 10 V, V _{GS} = 10 V	189		A
Drain-Source On-State Resistance ^a	r _{DS(on)}	V _{GS} = 10 V, I _D = 20 A	0.0484	0.049	Ω
		V _{GS} = 15 V, I _D = 20 A	0.0473	0.0485	
		V _{GS} = 10 V, I _D = 20 A, T _J = 100°C	0.0484		
		V _{GS} = 10 V, I _D = 20 A, T _J = 150°C	0.0914		
Forward Voltage ^a	V _{SD}	I _F = 20 A, V _{GS} = 0 V	0.91	0.86	V
Dynamic^b					
Input Capacitance	C _{iss}	V _{DS} = 25 V, V _{GS} = 0 V, f = 1 MHz	2953	2735	pF
Output Capacitance	C _{oss}		288	271	
Reverse Transfer Capacitance	C _{rss}		132	117	
Total Gate Charge ^c	Q _g	V _{DS} = 100 V, V _{GS} = 15 V, I _D = 50 A	70	75	nC
Gate-Source Charge ^c	Q _{gs}	V _{DS} = 100 V, V _{GS} = 10 V, I _D = 50 A	51	53	
Gate-Source Charge ^c	Q _{gs}		14	14	
Gate-Drain Charge ^c	Q _{gd}		17.5	17.5	

Notes

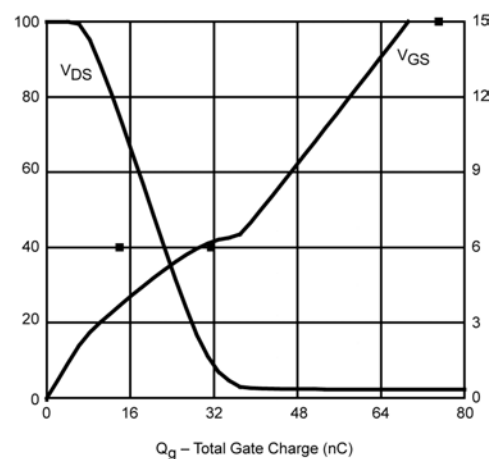
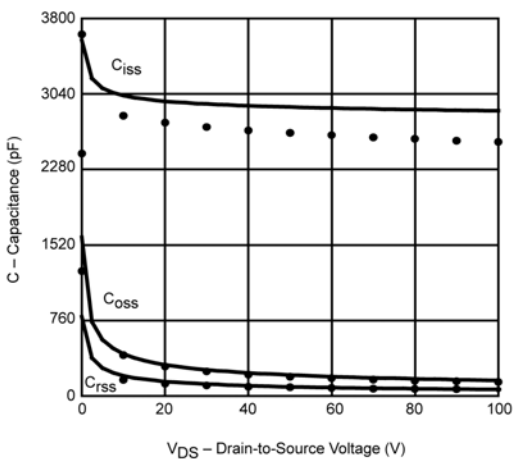
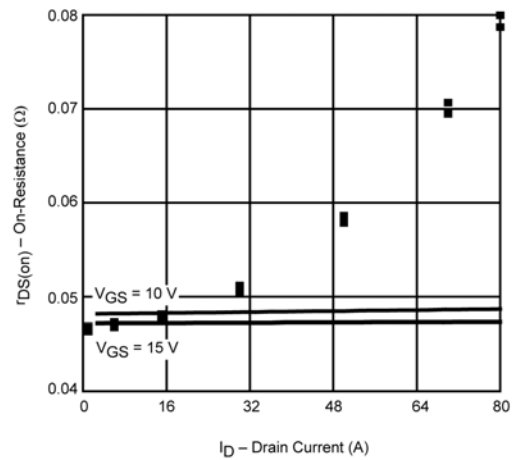
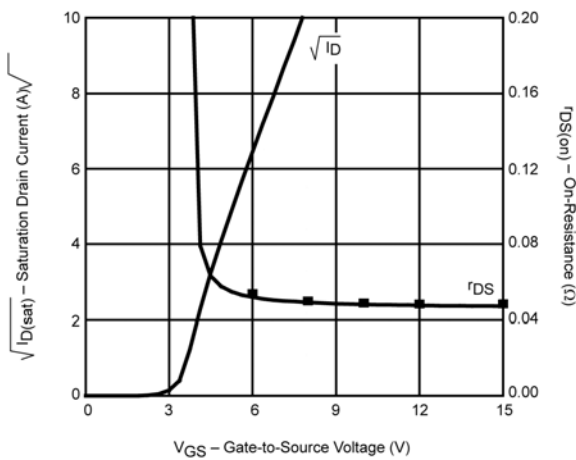
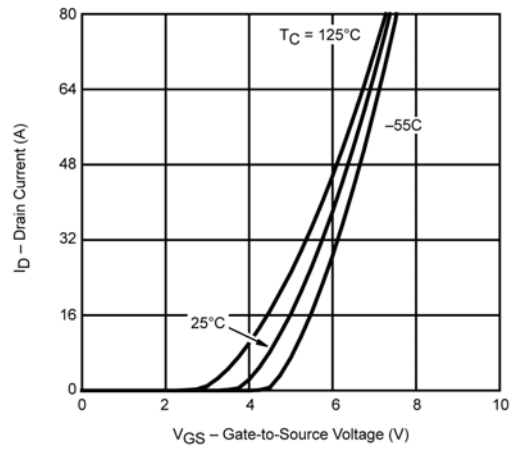
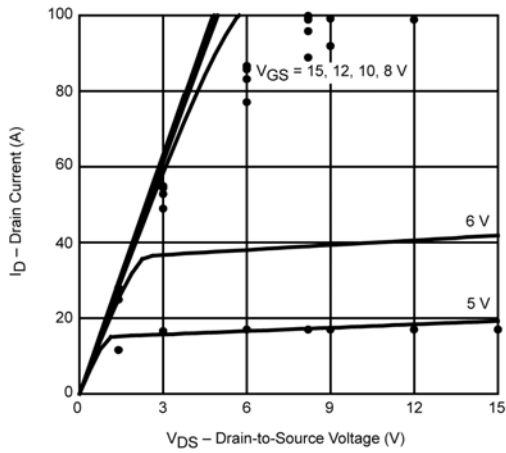
- Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
- Guaranteed by design, not subject to production testing.
- Independent of operating temperature.



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COMPARISON OF MODEL WITH MEASURED DATA ($T_J=25^\circ\text{C}$ UNLESS OTHERWISE NOTED)



Note: Dots and squares represent measured data.



Disclaimer

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